



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Steven T. Harshfield, et al.

Serial No.: 09/853,233

Filed: May 11, 2001

For: PCRAM MEMORY CELL AND  
METHOD OF MAKING SAME

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Group Art Unit: 2823

Examiner: Coleman, W.

Atty Docket: MICS:0061/FLE  
00-0535

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DEC 11 2002  
TECHNOLOGY CENTER 2800

Assistant Commissioner  
for Patents  
Washington, D.C. 20231

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I hereby certify that this correspondence is being deposited with the U.S. Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on the date below:	
December 4, 2002	<i>Helen Tinsley</i>
Date	Helen Tinsley

Sir:

**AMENDMENT AND RESPONSE**

In response to the Office Action mailed September 4, 2002, please amend the subject

Application, as follows:

**IN THE CLAIMS**

✓  
Please cancel claims 4, 22, 27, 34 and 41, without prejudice.

Please amend claims 1, 17-21, 26, 31 and 38, as follows:

- B<sup>1</sup>
1. (Once Amended) A memory cell comprising:  
a first line formed over a substrate, the first line being formed of a first conductive material that comprises one of aluminum, copper, nickel, and tungsten;